BRCS300P016ZJ

Rev.A Sep.-2022

DATA SHEET

DFN 2×2B-6L P MOS

P-Channel Enhancement Mode Field Effect Transistor in a DFN 2×2B-6L Plastic Package.

V_{DS} (V) = -16V I_D = -11A

$R_{DS(ON)}$@-4.5V⩽32mΩ

。HF Product.

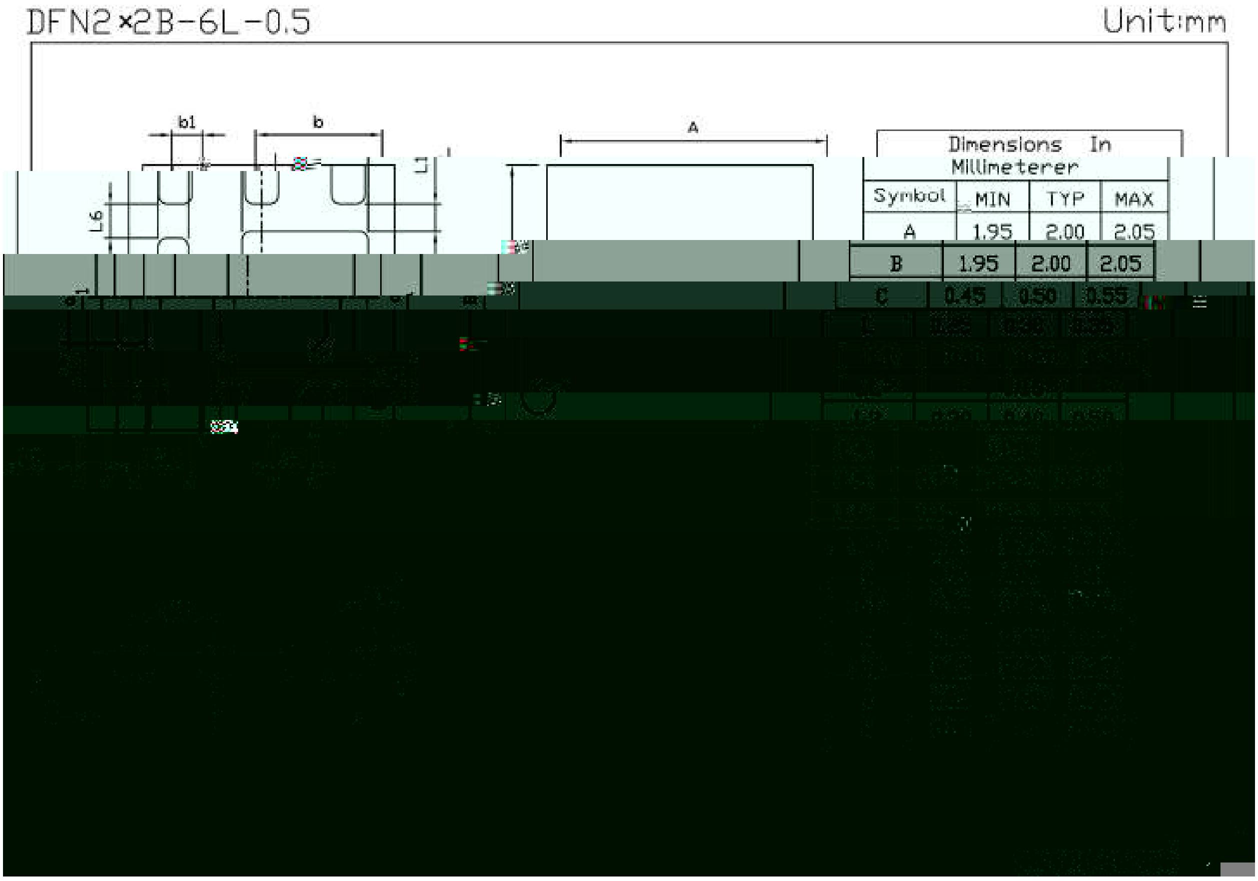
Power Management in Notebook computer, Portable Equipment and Battery powered systems.

/ Absolute Maximum Ratings(Tc=25)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-16	V
Gate-Source Voltage	V_{GSS}	±8	V
Continuous Drain Current	I_D	-11	A
Pulsed Drain Current	I_{DM}	-44	A
Avalanche Current	I_{AS}	21	A
Avalanche energy L=0.5mH	E_{AS}	308	mJ
Power Dissipation for Single Operation	P_D	15.5	W
Maximum Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 150	℃
Thermal Resistance-Junction to Ambient	$R_{\theta JC}$ t 10s	8	℃/W

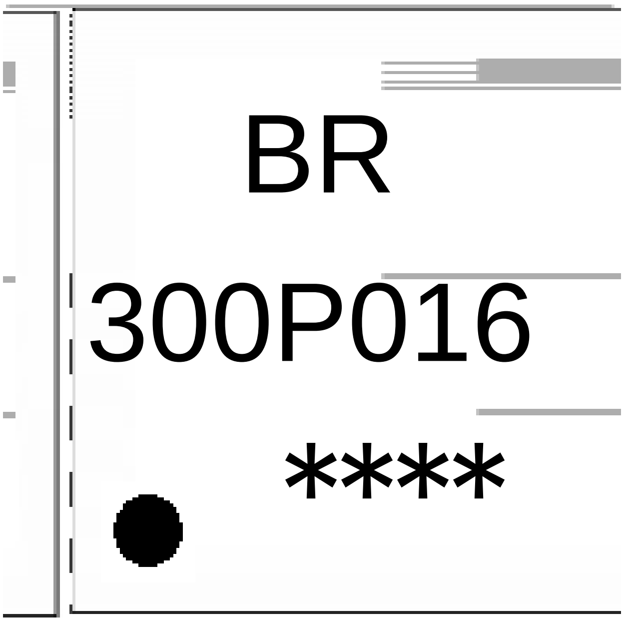
/ Package Dimensions

DFN2×2B-6L-0.5 外形尺寸图



Dimensions In Millimeterer			
Symbol	MIN	TYP	MAX
A	1.95	2.00	2.05
B	1.95	2.00	2.05
C	0.45	0.50	0.55
L	[illegible]	[illegible]	[illegible]

/ Marking Instructions



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300P016

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Note:

BR: Company Code

300P016: Product Type

****: Lot No. Code, code change with Lot No

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Note:

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